Power MOSFET

-20 V, -780 mA, Single P-Channel with ESD Protection, SOT-723

Features

- P-channel Switch with Low R_{DS(on)}
- 44% Smaller Footprint and 38% Thinner than SC-89
- Low Threshold Levels Allowing 1.5 V R_{DS(on)} Rating
- Operated at Low Logic Level Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

MAXIMUM RATINGS (T_J = $25^{\circ}C$ unless otherwise stated)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			V _{DSS}	-20	V	
Gate-to-Source Voltage			V _{GS}	± 6	V	
Continuous Drain	Steady State	$T_A = 25^{\circ}C$	Ι _D	-780	mA	
		$T_A = 85^{\circ}C$		-570		
	$t \le 5 s$	$T_A = 25^{\circ}C$		-870		
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	450	mW	
	$t \le 5 s$			550		
Continuous Drain	Steady	T _A = 25°C	I _D	-660	mA	
Current (Note 2)	State	T _A = 85°C		-480		
Power Dissipation (Note 2)		$T_A = 25^{\circ}C$	P _D	310	mW	
Pulsed Drain Cur- rent	t _p = 10 μs		I _{DM}	-1.2	А	
Operating Junction and Storage Tempera- ture			T _J , T _{STG}	–55 to 150	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

2. Surface mounted on FR4 board using the minimum recommended pad size



ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} TYP	I _D Max		
–20 V	0.38 Ω @ -4.5 V	–780 mA		
	0.52 Ω @ –2.5 V	–660 mA		
	0.70 Ω @ –1.8 V	–100 mA		
	0.95 Ω @ –1.5 V	–100 mA		





ORDERING INFORMATION

Device	Package	Shipping [†]		
NTK3139PT1G	SOT-723 Pb-Free	4000 / Tape & Reel		
NTK3139PT1H		4000 / Tape & Ree		
NTK3139PT5G		8000 / Tapa & Bool		
NTK3139PT5H		6000 / Tape & neer		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ hetaJA}$	280	°C/W
Junction-to-Ambient - t = 5 s (Note 3)	$R_{ hetaJA}$	228	
Junction-to-Ambient - Steady State Minimum Pad (Note 4)	$R_{\theta JA}$	400	

Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
Surface mounted on FR4 board using the minimum recommended pad size

MOSEET ELECTRICAL CHARACTERISTICS (T. - 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = -250 μ A		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	$I_D = -250 \ \mu A$, Reference to $25^{\circ}C$			-16.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -16V	$T_J = 25^{\circ}C$			-1.0	μΑ
			T _J = 125°C			-2.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±	4.5 V			±2.0	μΑ
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.45		-1.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				2.4		mV/°C
Drain-to-Source On Resistance		V _{GS} = -4.5 V, I _D = -780 mA			0.38	0.48	Ω
		V _{GS} = -2.5 V, I _D = -660 mA			0.52	0.67	
	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -100 mA			0.70	0.95	
		$V_{GS} = -1.5$ V, $I_D = -100$ mA			0.95	2.20	
Forward Transconductance	9fs	V _{DS} = -10 V, I _D = -540 mA			1.2		S
CHARGES, CAPACITANCES AND	GATE RESISTAN	NCE		-	-		
Input Capacitance	C _{ISS}				113	170	
Output Capacitance	C _{OSS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = –16 V			15	25	pF
Reverse Transfer Capacitance	C _{RSS}				9.0	15	
SWITCHING CHARACTERISTICS,	V _{GS} = 4.5 V (Not	e 6)		-	-		
Turn On Delay Time	t _{d(ON)}				9.0		
Rise Time	t _r	V_{GS} = -4.5 V, V_{DS} = -10 V, I_{D} = -200 mA, R_{G} = 10 Ω			5.8		ns
TurnOff Delay Time	t _{d(OFF)}				32.7		
Fall Time	t _f				20.3		
DRAIN SOURCE DIODE CHARACT	ERISTICS			-	-		
Forward Diode Voltage	V _{SD}	V_{GS} = 0 V, I _S = -350 mA	$T_J = 25^{\circ}C$		-0.8	-1.2	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, d _{ISD} /d _t = 100 A/µs, I _S = -1.0 A, V _{DD} = -20 V			13.2		ns
Charge Time	ta				11.8		1
Discharge Time	t _b				1.4		1
Reverse Recovery Charge	Q _{RR}				5.0		nC

5. Pulse Test: pulse width = 300 μ s, duty cycle = 2% 6. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and **W** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemic.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components insystems intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death massociated with such unintended or unauthorized applicable copyright laws and is not for resade in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative



Authorized Distribution Brand :



Website :

Welcome to visit www.ameya360.com

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

- > Sales :
 - Direct +86 (21) 6401-6692
 - Email amall@ameya360.com
 - QQ 800077892
 - Skype ameyasales1 ameyasales2

> Customer Service :

Email service@ameya360.com

> Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com